QDLASER QLF101A-AA

1060 nm Gain Chip

C00075-03 June 2014



1. DESCRIPTION

The QLF101A-AA is a 1060-nm band gain chip suitable for a wide-band tunable light source.

2. FEATURES

- Wide tuning band
- Low facet reflectance with angled facet structure

3. APPLICATION

- Tunable external cavity lasers
- Wide band light source

4. ABSOLUTE MAXIMUM RATING

| PARAMETER | SYMBOL | RATING | UNIT |
|-------------------------------|---------------------------|-----------|------|
| Optical Output power | \mathbf{P}_{f} | 80 | mW |
| LD Forward Current | $I_{\rm F}$ | 250 | mA |
| LD Reverse Voltage | V _{RLD} | 2 | V |
| Storage Temperature * | T_{stg} | -40 to 85 | °C |
| Soldering Temperature (<1.5s) | T_{sld} | 390 | °C |

* No condensation

5. OPTICAL AND ELECTRICAL CHARACTERISTICS

| | | | $(T_{LD} = 25^{\circ}C, \text{ unless otherwise specified})$ | | | |
|----------------------------------|---------------------|----------------------------|--|------|------|------|
| PARAMETER | SYMBOL | TEST CONDITION | MIN | TYP | MAX | UNIT |
| Center Wavelength | λ_{c} | CW, I _f =100 mA | 1040 | 1060 | 1080 | nm |
| Optical Bandwidth@3dB | Δν | CW, I _f =100 mA | 30 | 43 | - | nm |
| Gain Ripple (RMS) | - | CW, $I_f = 100 \text{ mA}$ | - | TBD | - | dB |
| ASE Power | P _{ASE} | CW, $I_f = 100 \text{ mA}$ | 9 | 10 | - | mW |
| Operation Current | I _{op} | CW | - | 100 | 180 | mA |
| Operation Voltage | V _{op} | CW, If =100 mA | - | 1.7 | 2.2 | V |
| Beam Divergence (FWHM) | θ⊥ | CW, If =100 mA | - | 35 | - | deg. |
| | θ,,, | CW, If =100 mA | - | 15 | - | deg. |
| Facet Reflectance (Angled facet) | R _{angle} | at 1060 nm | - | - | 0.01 | % |
| Facet Reflectance (Normal facet) | R _{normal} | at 1060 nm | - | 7.5 | - | % |
| Operation Temperature | T _{chip} | = | 20 | _ | 30 | °C |

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6. OUTLINE DRAWING



7. NOTICE

• Safety Information

This product is classified as Class 3B laser product, and complies with 21 CFR Part 1040.10. Please do not take a look at laser lighting in operations since laser devices may cause troubles to human eyes. Please do not eat, burn, break and make chemical process of the products since they contain GaAs material.

• Handling products

Semiconductor lasers are easily damaged by external stress such as excess temperature and ESD.

Please pay attention to handling products, and use within range of maximum ratings.

QD Laser takes no responsibility for any failure or unusual operation resulting from improper handling, or unusual physical or electrical stress.

• RoHS

This product conforms to RoHS compliance related EU Directive 2002/95/EC.

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